

MDL-NS-852/1-150mW



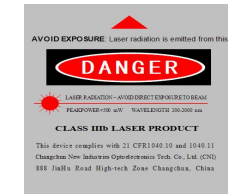
**NANOSECOND PULSED
INFRARED DIODE LASER
AT 852nm**

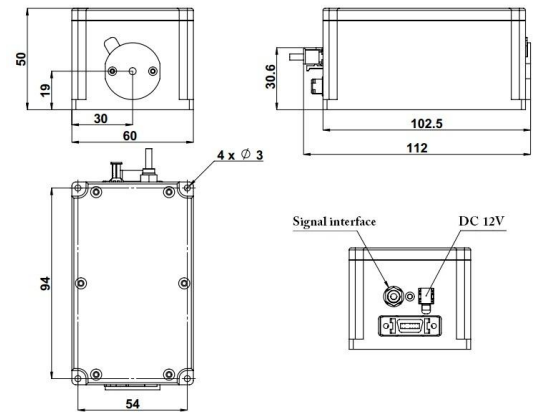
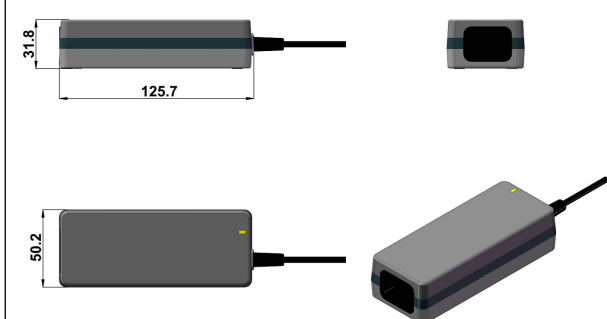
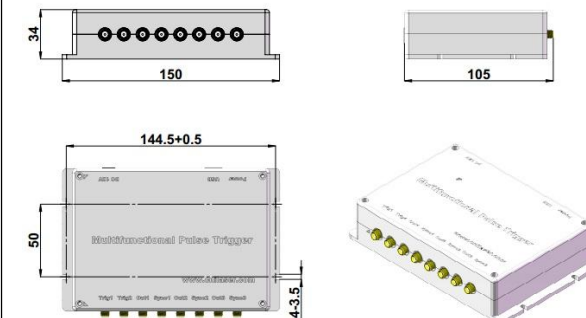
This series laser products with excellent material removal rate, are widely used in microelectronics, material processing, solar energy and medical equipment manufacturing, etc.



SPECIFICATIONS

Central wavelength (nm)	852±10
Operating mode	Pulsed
Peak power (mW) ¹	1-150
Power stability (rms, 4 hours ± 3°C)	<2%, <1%, <0.5%
Pulse width (FWHM)	10ns-10ms
Transverse mode	Near TEM ₀₀
M ²	<1.5
Beam diameter at the aperture (1/e ² ,mm)	~4.0
Beam divergence, full angle (mrad)	<1.0
Rep. rate ²	DC-30MHz
Rise Time (ns)	<4
Fall Time (ns)	<3
Modulation Depth (extinction ratio)	>1000000:1
Warm-up time (minutes)	<5
Cooled method	Conduction
Beam height from base plate (mm)	19
Operating temperature (°C)	10-35
Operating voltage (VDC)	12V/3.34A
Expected lifetime (hours)	>10000



LASER HEAD (DRIVER Integrated) ³	POWER SUPPLY (100-240VAC) optional	MULTIFUNCTIONAL PULSE TRIGGER optional
 <p>112 (L) × 60 (W) × 50 (H) mm³, 0.5kg</p>	 <p>125.7 (L) × 50.2 (W) × 31.8 (H) mm³, 0.3kg</p>	 <p>150 (L) × 105 (W) × 34 (H) mm³, 0.5kg</p>

1 Any power level can be selected in this range.

2 Both internal and external triggers are acceptable. The internal trigger supports a frequency range of DC-25MHz.

3 RS232 control optional, output power adjustable 10-100% by software.